arXiv:1605.03684v1 [cond-mat.mtrl-sci] 12 May 2016

Density Functional Theory study on the electronic structure and thermoelectric properties of strained Mn_4Si_7

Do Duc Cuong, JinSik Park, S. H. Rhim,* and Soon Cheol Hong†

Department of Physics and Energy Harvest Storage Research Center, University of Ulsan, Ulsan, 680-749, Republic of Korea

Joo-Hyong Lee

School of Materials Science and Engineering, Gwangju Institute of Science and Technology, Gwangju, Republic of Korea

Abstract

Strain effect on electronic structure and thermoelectric properties of higher manganese silicides (HMS) Mn_4Si_7 was studied using density functional theory (DFT) and through solving Boltzman transport equation (BTE). We found that tensile strain reduces band gap while compressive strain does not much affect the band gap. Seebeck coeficient increases with temperature, which is consistent with experiments. The electrical conductivity and power factor show anisotropy, where in-plane direction is more dominant. Anisotropy of the electrical conductivity along in-plane and out of plane direction was explained due to change of band dispersion in the valence band maximum (VBM).

PACS numbers:

Keywords: Thermoelectric, Seebeck coefficient, Density Functional Theory

*Electronic address: sonny@ulsan.ac.kr

†Electronic address: schong@ulsan.ac.kr

I. INTRODUCTION

Search for new source of energy has been rapidly increased recently with high demand because of high price and possible exhaustion of traditional energy sources such as fossil fuel, gaseous. On the other hand, the use of current system is not so effective as up to 60% of energy is wasted as heat [1]. In searching the new source of energy, thermoelectric materials receive a lot of interests owing to its capability to convert thermal energy into electrical energy. The thermoelectric materials have many advantages: there is no moving part with high durability, and they are environmetally friendly green energy. However, the current state of art of thermoelectrics is limited in wide-scale applications because of low conversion efficiency and high material costs. The effciciency of thermoelectric materials is strongly related to dimensionless figure of merit, which is defined by $ZT = \frac{\sigma S^2}{\kappa}T$, where σ, S, κ, and T are the electrical conductivity, the Seebeck coefficient, the thermal conductivity, and the absolute temperature, respectively[2]. Some materials having high ZT such as Bi_2Te_3, PbTe, and Zn_4Sb_3, however, contain toxic elements or have high cost elements (Te, Sb) [3]. Higher Manganese Silides (HMS), $MnSi_\delta$, have been considered as alternative promissing thermoelectric materials because they exhibit relative high ZT, contains two abundant and non-toxic elements. Furthermore, they possess mechanical stability to corrosion and oxidation [4, 5]. Depending on δ value, several closely related phases such as Mn_4Si_7, $Mn_{11}Si_{19}$, and $Mn_{15}Si_{26}$, have been identified in this class of material[6, 7].

There have been a number of studies on thermoelectric properties of HMS. Due to rather low thermal conductivity, high Seebeck coefficent, and electrical conductivity, the ZT of HMS is relatively high, whose range is 0.4-0.75 [3, 8, 9]. The improvement of the ZT in the HMS seems fascinating. In this study, the strain effect on the electronic structure and thermoelectric properties of HMS has been investigated using first-principles calculations and Boltzman Transport equation (BTE).

II. METHODOLOGY

First-principles density functional calculations are performed using Vienna *Ab Initio* Simulation Package (VASP)[10]. For the exchange-correlation potential, generalized gradient approximation (GGA) is employed with Perdew, Burke, and Ernzerhof (PBE)

parametrization[11, 12] with projected augmented wave (PAW) basis sets[13]. Cutoffs for kinetic energy is chosen 400 eV. The Brillouin-zone (BZ) integration is done with 6×6×2 k mesh in Monkhorst-Pack scheme. BoltzTrap[14] is used interpolate band eigenvalues to extract velocities, which is based on the converged electronic structure. The thermoelectric properties are calculated based on the interpolation on k grid of 12×12×4 giving 144 k point in the irreducible Brillouin zone wedge. Throughout this paper, we consider Mn_4Si_7, where δ=1.75.

III. RESULTS AND DISCUSSION

Mn_4Si_7 is well-known as a degenerate $p-$type semiconductor with hole carrier concentration of order of $10^{21} cm^{-3}$. Crystal structure belongs to the well-known Nowotny Chimney-Ladder compounds, consisting of two sublattices : Manganese "chimney" sublattice and Silicon "ladder" sublattice [15]. Calculated lattice constants are $a = 5.508$ $\AA$ and $c/a = 3.158$, which agrees well with experiments and other previous calculations [15–17]. The electronic band structure of Mn_4Si_7 show semiconducting behavior with indirect band gap of 0.82 eV between Γ-points in VCBM and Z-point in CBM, also consistent with previous calculations [17, 18]

To study the strain effect, the different strain is applied from -3% (compressive strain) to +3% (tensile strain) along x-axis (a) and y-axis (b) respect to the unstrained lattice. Lattice constant along z-axis (c) is optimized for each set of lattice constant along x- and y-axis. As a result, change of c is from 5.1% to -4.4%, compared to unstrained lattice, This change of c leads to the increase of volume from -4.2% to +4.4% as shown in Fig. 1(a).

The change in band gap is more dramatic as shown in Fig. 1(b). The band gap is not much changed under compressive strain, but does change under the tensile strain. The band gap is reduced from 0.82 eV to 0.77 eV at +3% tensile strain with respect to the unstrained one. This trend in band gap change is totally different from other materials such as SnSe, where the band gap was found to increase due to the increasing of lattice separation along z direction [19].

In Fig. 1(c) and (d), we show the comparison of band structure of compressive (-3%) and tensile strain (+3%) case. Other strains are not shown here but the general trends are similar. The band structure topology is alsmost same under applying strain, except for band

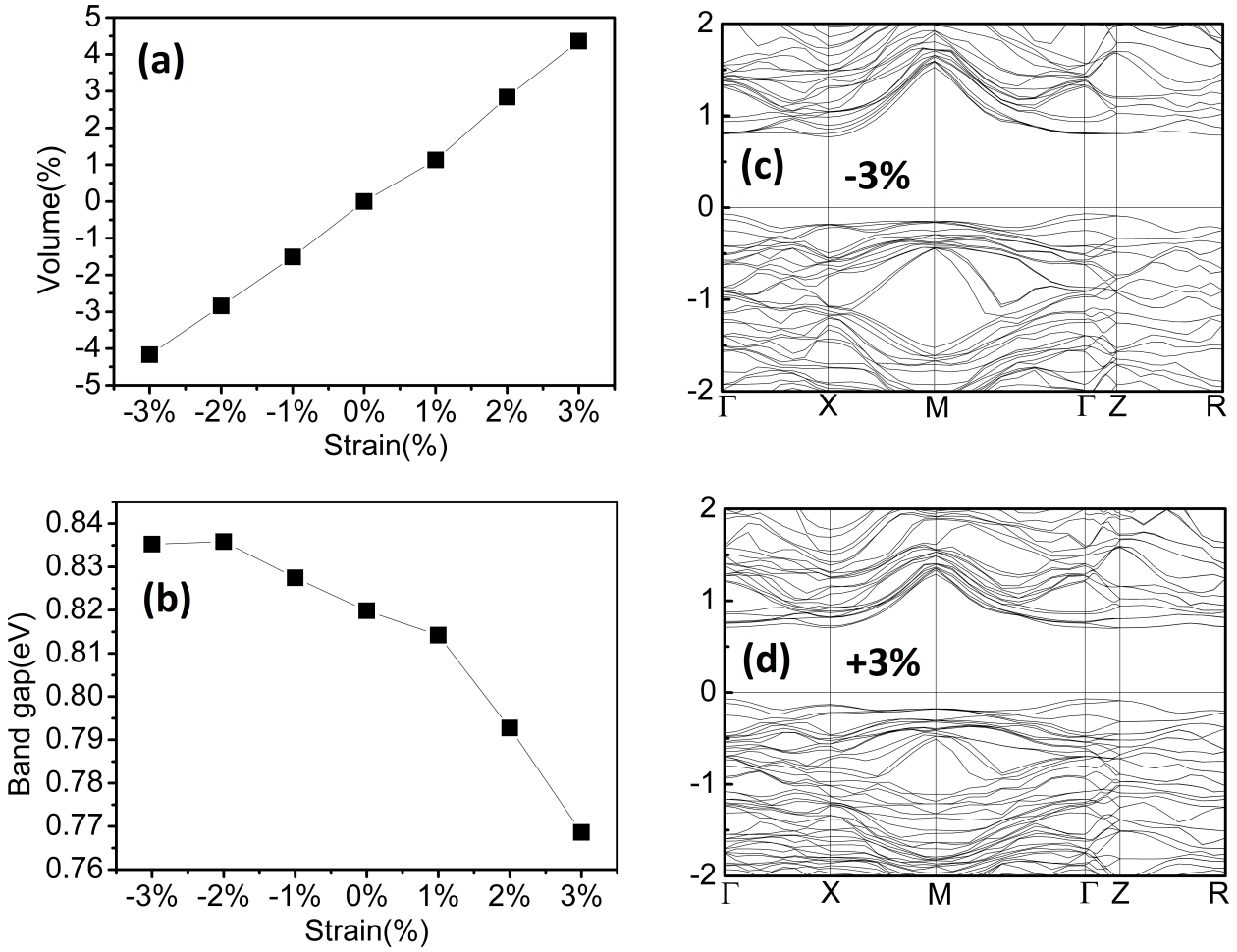

FIG. 1: Dependence of volume (a) and band gap (b) with different strain from -3% to +3% and electronic band structure of Mn_4Si_7 in -3% compressive strain (c) and +3% tensile strain (d).

gap. This behavior can be predictable due to the fact that the properties of HMS Mn_4Si_7 is stable under ambient conditions as reported in previous experiments [4, 5]. The band dispersion on VBM along the $\Gamma - Z$ direction is quite flat compared to along the $\Gamma - X$ direction. However, under applying compressive strain, the band along $\Gamma - Z$ on VBM is slightly more dispersive, while it is less dispersive along $\Gamma - X$ direction. This change of band dispersion will affect the electrical conductivity which will be discussed later.

The Seebeck coefficient, electrical conductivity σ/τ, and power factor $PF/\tau = \sigma/\tau.S^2$ were calculated and showed in Fig. 2 as the function of temperature, where τ is relaxation time. In all calculations, the hole carrier concentration was fixed at experimental value $10^{21} cm^{-3}$ [8]. The Seebeck coefficient in unstrained Mn_4Si_7 increases with increasing temperature, which show very good agreement with experimental data [8], However, the

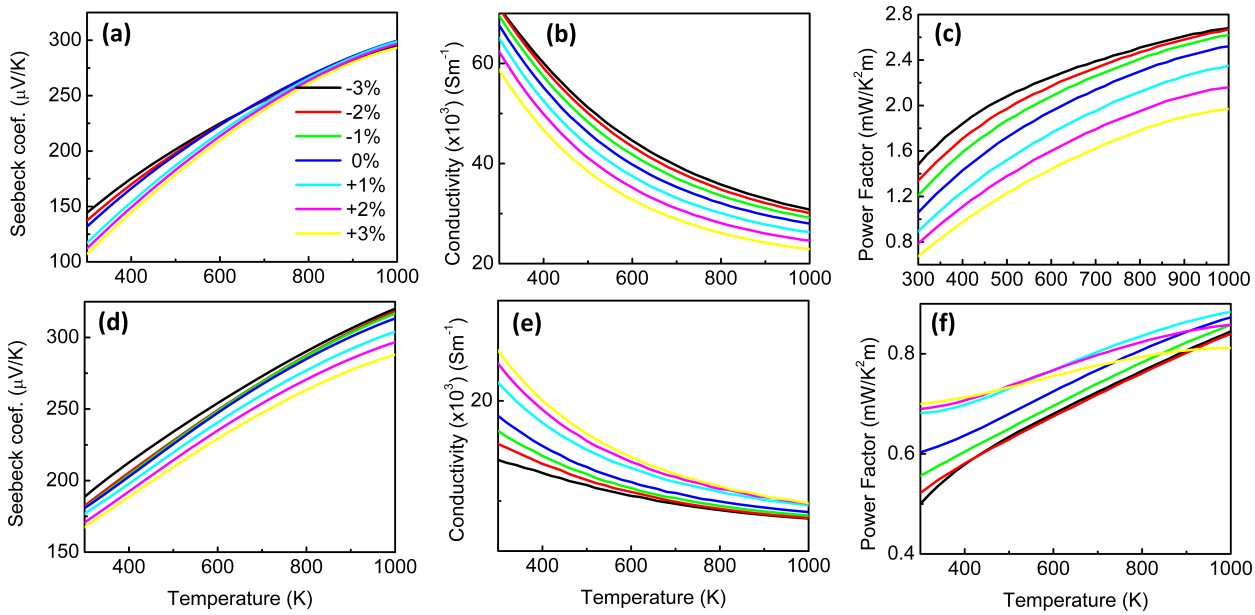

FIG. 2: The effect of strain on the thermoelectric properties of Mn_4Si_7: The Seebeck coefficient (a), electrical conducivity σ/τ (b) and Power factor (c) along in-plane direction. The Seebeck coefficient (d), electrical conductivity σ/τ (e) and Power factor (f) along out of plane direction.

electrical conductivity σ/τ show highly anisotropic, where the σ/τ along the in-plane direction is almost three times bigger compared with that along out of plane direction. The large difference between in-plane and out of plane electrical conductivity come from the difference in band dispersion on the VBM which we discussed above, because the electrical conductivity is proportional to the electron verlocity, which is defined as the derivate of energy band versus the k-vector [14]. As a result, the PF/τ along in-plane lattice is much higher compared with along out of plane lattice.

Under the strain, the Seebeck coefficient does not change very much in both in-plane and out of plane direction. However, the behavior of electrical conductivity is quite different and exhibits some anisotropy. Due to the change of band dispersion in the VBM, the σ/τ show different behavior, σ/τ along in-plane direction decreases under the tensile strain, and increase under the compressive strain. While, σ/τ along out-of-plane direction is reduced under the compressive strain and increases under the tensile strain. As a results, the power factor (PF) show the same trend with the electrical conductivity. It is noticeable that, even reduction in the out-of-plane lattice, the PF along the in-plane lattice is more dominant. Therefore, the increase of PF along this direction leads to increase the overall PF and ZT.

IV. CONCLUSION

The strain effect on the electronic structure and thermoelectric properties of Mn_4Si_7 has been studied using Density functional theory calculations and solving Boltzman Transport Equation. The Seebeck coefficient increases with temperature. Both the electrical conductivity and PF increase along the in-plane direction, and decrease along out-of-plane direction as a result of band dispersion change at the VBM. We also suggest that the compressive strain can improve PF and ZT of Mn_4Si_7.

V. ACKNOWLEDGEMENT

This work is supported by a grant from Energy Efficiency & Resource program of the Korea Institute of Energy Technology Evaluation and Planning (KETEP) funded by the Korean Ministry of Knowledge Economy (20132020000110), and Priority Research Centers Program (2009-0093818) through the NRF funded by the Ministry of Education.

---

[1] Kunihito Koumoto, Ichiro Terasaki, and Ryoji Funahashi. MRS Bulletin **31**,206–210 (2006).

[2] Jiaqing He, Mercouri G. Kanatzidis, and Vinayak P. Dravid. Materials Today **16**, 166 – 176 (2013).

[3] Steven N. Girard, Xi Chen, Fei Meng, Ankit Pokhrel, Jianshi Zhou, Li Shi, and Song Jin. silicides grown by chemical vapor transport. Chemistry of Materials**26**, 5097–5104 (2014).

[4] I. Nishida. Journal of Materials Science **7**, 435–440 (1972).

[5] Alan W. Searcy. Journal of the American Ceramic Society **40**, 431–435 (1957).

[6] Ingvar Engstrom and Bertil Lonnberg. Journal of Applied Physics **63**, 4476–4484 (1988).

[7] V. Ponnambalam and DonaldT. Morelli. Journal of Electronic Materials **41**, 1389–1394 (2011).

[8] Yatir Sadia and Yaniv Gelbstein. Journal of Electronic Materials **41**, 1504–1508 (2012).

[9] Q. R. Hou, W. Zhao, Y. B. Chen, D. Liang, X. Feng, H. Y. Zhang, and Y. J. He. physica status solidi (a) **204**, 3429–3437 (2007).

[10] G. Kresse and J. Hafner. Phys. Rev. B **47**, 558–561 (1993).

[11] John P. Perdew, J. A. Chevary, S. H. Vosko, Koblar A. Jackson, Mark R. Pederson, D. J. Singh, and Carlos Fiolhais. Phys. Rev. B **46**, 6671–6687 (1992).

[12] John P. Perdew, Kieron Burke, and Matthias Ernzerhof. Phys. Rev. Lett. **77**, 3865–3868 (1996).

[13] P. E. Blöchl. Phys. Rev. B **50**, 17953–17979 (1994).

[14] Georg K.H. Madsen and David J. Singh. Computer Physics Communications **175**, 67 – 71 (2006).

[15] Yuzuru Miyazaki, Dai Igarashi, Kei Hayashi, Tsuyoshi Kajitani, and Kunio Yubuta. Phys. Rev. B **78**, 214104 (2008).

[16] T. Kajitani, K. Yubuta, T. Shishido, and S. Okada. Journal of Electronic Materials **39**, 1482–1487 (2010).

[17] D. B. Migas, V. L. Shaposhnikov, A. B. Filonov, V. E. Borisenko, and N. N. Dorozhkin. Phys. Rev. B, **77**, 075205 (2008).

[18] S. Caprara, E. Kulatov, and V.V. Tugushev. The European Physical Journal B **85**, 149 (2012).

[19] Do Duc Cuong, S. H. Rhim, Joo-Hyong Lee, and Soon Cheol Hong. AIP Advances **5**, 117147 (2015).